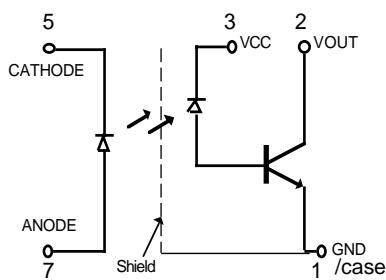
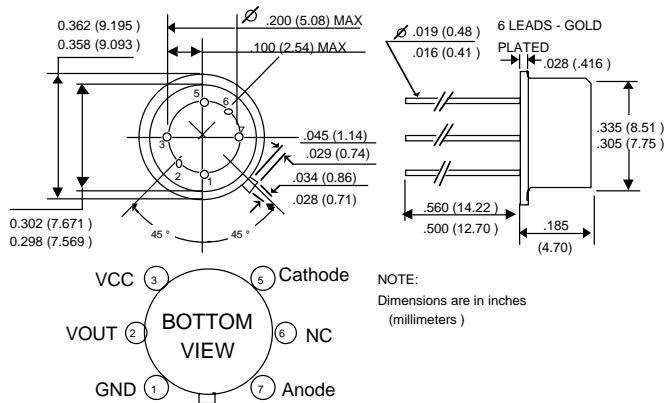




ISO LINK



SCHEMATIC



PACKAGE OUTLINE

Features

- ◆ Electrical parameters guaranteed over -55°C to +125°C ambient temp. range
- ◆ 1000 Vdc electrical isolation
- ◆ High-Speed, 1 Mbit/s typical
- ◆ Open collector output
- ◆ 300 KHz bandwidth
- ◆ TO - 5 hermetic package
- ◆ Similar to 6N135/136, 4N55
- ◆ Radiation tolerant
- ◆ 100% hi-rel screening are offered

Description

The OLH 300 is suitable for interfacing TTL to LSTTL, TTL or CMOS as well as wide bandwidth analog applications. Each OLH 300 has a light emitting diode and an integrated photo-diode transistor detector mounted and coupled in a ceramic substrate inside a hermetic TO-5 package providing 1000 Vdc electrical isolation between input and output. The integrated photo-diode transistor improves switching speed by orders of magnitude as compared to standard photo transistors, by reducing the base to collector capacitance. The internal shield provides excellent common-mode immunity performance.

NOTES:

1. Measured between pins 1,2 and 3 shorted together and pins 5,6 and 7 shorted together. $T_A = 25^\circ\text{C}$ and duration = 1 second.
2. Current transfer ratio is define as the ratio of output collector current, I_C to the forward LED current, I_F times 100%

Absolute Maximum Ratings

Couple							
Input to Output Isolation Voltage ¹						± 1000 Vdc	
Storage Temperature Range						-65°C to +150°C	
Operation Temperature Range						-55°C to +125°C	
Lead Temperature 1.6 mm from case for 10 sec.						240°C	
Input Diode							
Average Input Current						20 mA	
Peak Forward Current ($\leq 1\text{mS}$ duration)						40 mA	
Reverse Voltage						5.0 V	
Power Dissipation						36 mW	
Output Detector							
Average Output Current						8 mA	
Peak Output Current						16 mA	
Supply Voltage, V _{cc}						-0.5 V to 18 V	
Output Voltage, V _{out}						-0.5 V to 18 V	
Power Dissipation						50 mW	

ELECTRICAL CHARACTERISTIC ($T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$, Unless Otherwise Specified)

Parameter	Symbol	Min	Typ.	Max	Units	Test Conditions	Fig.	Note
Current Transfer Ratio	CTR	20	45		%	$I_F=10 \text{ mA}, V_o=0.4 \text{ V}, V_{cc}=4.5 \text{ V},$	2	2
Logic Low Output Voltage	V _{OL}		.25	0.4	V	$I_F=10 \text{ mA}, I_{O_L}=1.5 \text{ mA}, V_{cc}=4.5 \text{ V}$		
Logic High Output Current	I _{OH}		.05	100	μA	$I_F=0 \text{ mA}, V_o=V_{cc}=15 \text{ V}$		
Supply Current								
Logic Hi	I _{CCL}		40	200	μA	$I_F=10 \text{ mA}, V_{cc}=15 \text{ V}, V_o=\text{open}$		
Logic Low	I _{CCH}		.05	10	μA	$I_F=0 \text{ mA}, V_{cc}=15 \text{ V}, V_o=\text{open}$		
Input Forward Voltage	V _F		1.7	2.5	V	$I_F=10 \text{ mA}$		
Temperature Coefficient of input diode Forward Voltage	$\frac{\Delta V_F}{\Delta T_A}$		-2.3		mV/ $^\circ\text{C}$	$I_F=5 \text{ mA}$	1	
Input Reverse Breakdown Voltage	B _{VR}	3			V	$I_R=10 \mu\text{A}$		
Input to Output Leakage Current	I _{I-O}			1.0	μA	Relative Humidity $\leq 50\%$, $T_A = 25^\circ\text{C}, V_{I-O} = 1000 \text{ Vdc}$	1	
Propagation Delay Time Logic High to Low	t _{PHL}		0.3	1.0	μS	$I_F=10 \text{ mA}, V_{cc}=5 \text{ V}, R_L=4.1 \text{ k}\Omega,$	3,4	
Propagation Delay Time Logic Low to High	t _{PLH}		0.5	2.0	μS	$I_F=10 \text{ mA}, V_{cc}=5 \text{ V}, R_L=4.1 \text{ k}\Omega,$	3,4	

ALL TYPICAL @ $T_A = 25^\circ\text{C}$

TYPICAL PERFORMANCE CURVES

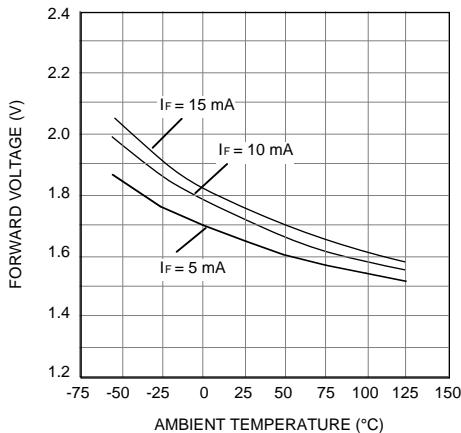


Fig. 1 -LED Forward Characteristics

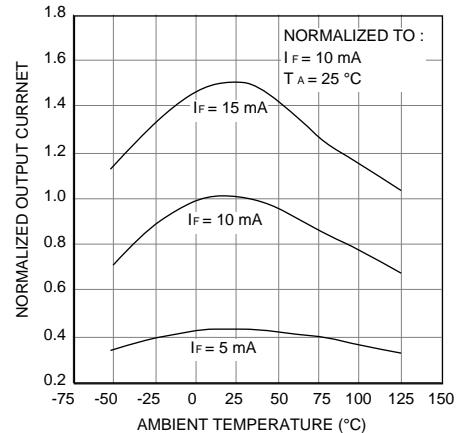


Fig. 2 - Normalized Output Current
vs. I_F vs. Temperature

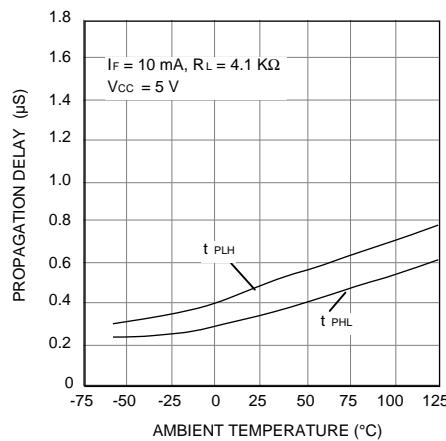


Fig. 3 - Propagation Delay vs.
Temperature

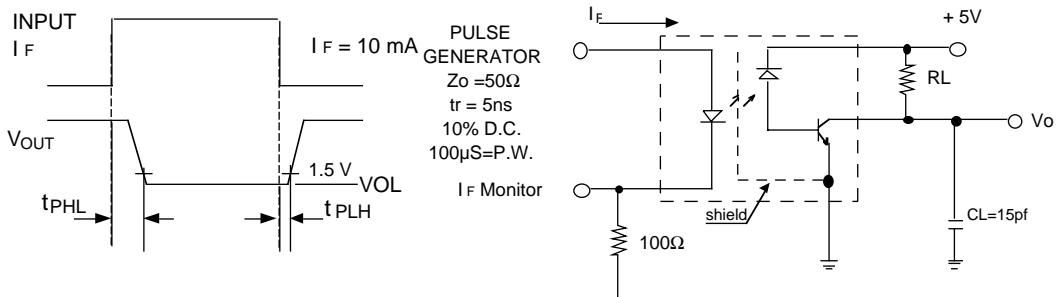


Fig. 4 - Switching Test Circuit